

NTHD5903T1

Power MOSFET Dual P-Channel ChipFET™

2.1 Amps, 20 Volts

Features

- Low $R_{DS(on)}$ for Higher Efficiency
- Logic Level Gate Drive
- Miniature ChipFET Surface Mount Package Saves Board Space

Applications

- Power Management in Portable and Battery-Powered Products; i.e., Cellular and Cordless Telephones and PCMCIA Cards

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	5 secs	Steady State	Unit
Drain-Source Voltage	V_{DS}	-20		V
Gate-Source Voltage	V_{GS}	± 12		V
Continuous Drain Current ($T_J = 150^\circ\text{C}$) (Note 1) $T_A = 25^\circ\text{C}$ $T_A = 85^\circ\text{C}$	I_D	± 2.9 ± 2.1	± 2.1 ± 1.5	A
Pulsed Drain Current	I_{DM}	± 10		A
Continuous Source Current (Diode Conduction) (Note 1)	I_S	-1.8	-0.9	A
Maximum Power Dissipation (Note 1) $T_A = 25^\circ\text{C}$ $T_A = 85^\circ\text{C}$	P_D	2.1 1.1	1.1 0.6	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150		$^\circ\text{C}$

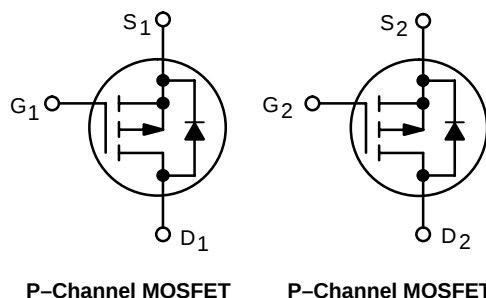
1. Surface Mounted on 1" x 1" FR4 Board.



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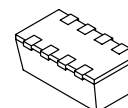
<http://onsemi.com>

DUAL P-CHANNEL
2.1 AMPS, 20 VOLTS
 $R_{DS(on)} = 155 \text{ m}\Omega$



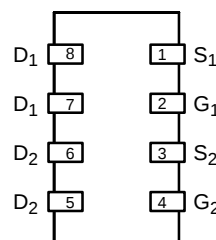
P-Channel MOSFET

P-Channel MOSFET

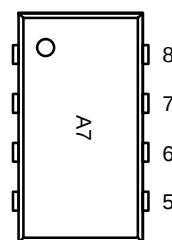


ChipFET
CASE 1206A
STYLE 2

PIN CONNECTIONS



MARKING DIAGRAM



A7 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping
NTHD5903T1	ChipFET	3000/Tape & Reel

NTHD5903T1

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Maximum Junction-to-Ambient (Note 2) $t \leq 5$ sec Steady State	R_{thJA}	50 90	60 110	$^{\circ}\text{C/W}$
Maximum Junction-to-Foot (Drain) Steady State	R_{thJF}	30	40	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
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Static

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-0.6	—	—	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	—	—	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-1.0	μA
		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 85^{\circ}\text{C}$	—	—	-5.0	
On-State Drain Current (Note 3)	$I_{D(on)}$	$V_{DS} \leq -5.0 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10	—	—	A
Drain-Source On-State Resistance (Note 3)	$r_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -2.1 \text{ A}$	—	0.130	0.155	Ω
		$V_{GS} = -3.6 \text{ V}, I_D = -2.0 \text{ A}$	—	0.150	0.180	
		$V_{GS} = -2.5 \text{ V}, I_D = -1.7 \text{ A}$	—	0.215	0.260	
Forward Transconductance (Note 3)	g_{fs}	$V_{DS} = -10 \text{ V}, I_D = -2.1 \text{ A}$	—	5.0	—	S
Diode Forward Voltage (Note 3)	V_{SD}	$I_S = -0.9 \text{ A}, V_{GS} = 0 \text{ V}$	—	-0.8	-1.2	V

Dynamic (Note 4)

Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -2.1 \text{ A}$	—	3.0	6.0	nC
Gate-Source Charge	Q_{gs}		—	0.9	—	
Gate-Drain Charge	Q_{gd}		—	0.6	—	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10 \text{ V}, R_L = 10 \Omega, I_D \cong -1.0 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_G = 6 \Omega$	—	13	20	ns
Rise Time	t_r		—	35	55	
Turn-Off Delay Time	$t_{d(off)}$		—	25	40	
Fall Time	t_f		—	25	40	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -0.9 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	—	40	80	

2. Surface Mounted on 1" x 1" FR4 Board.

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL CHARACTERISTICS

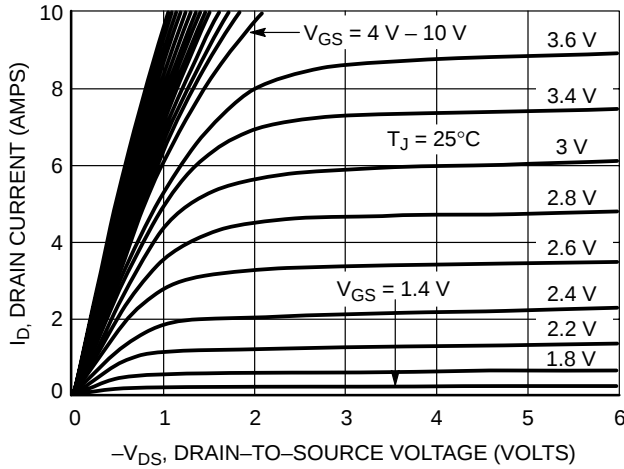


Figure 1. On-Region Characteristics

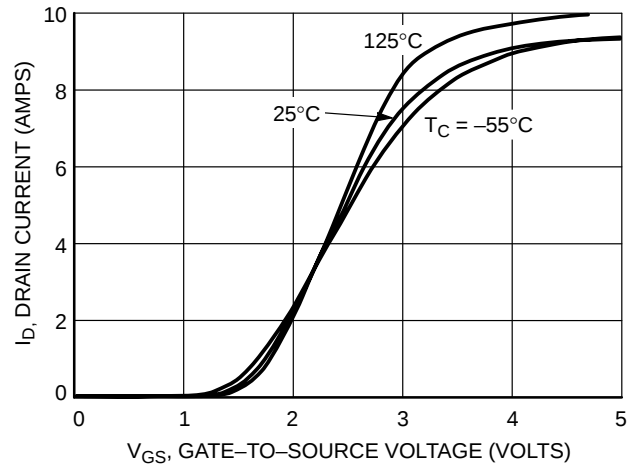


Figure 2. Transfer Characteristics

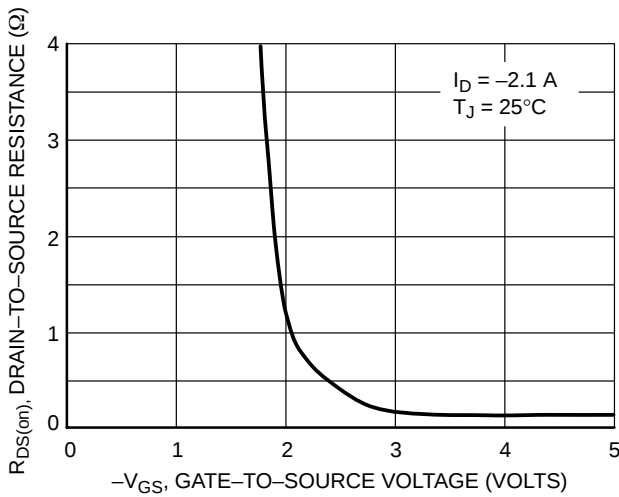


Figure 3. On-Resistance vs. Gate-to-Source Voltage

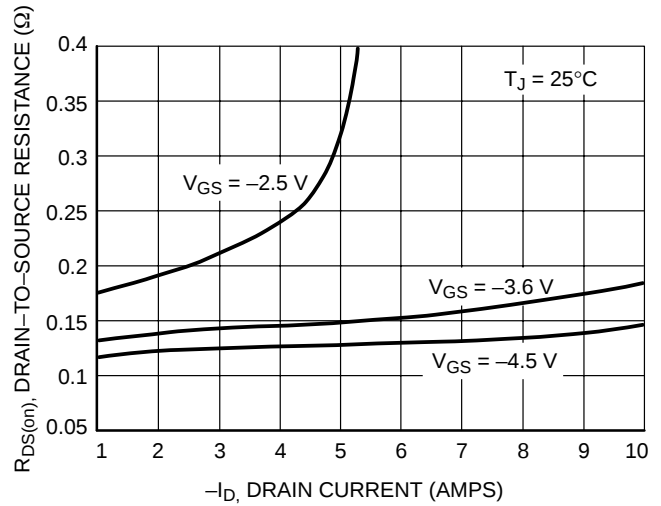


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

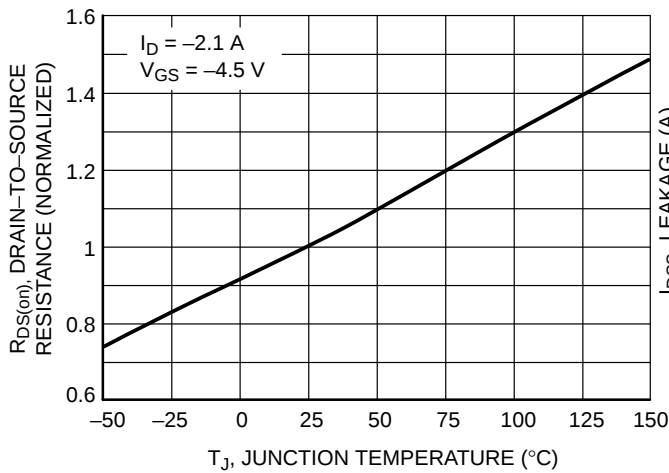


Figure 5. On-Resistance Variation with Temperature

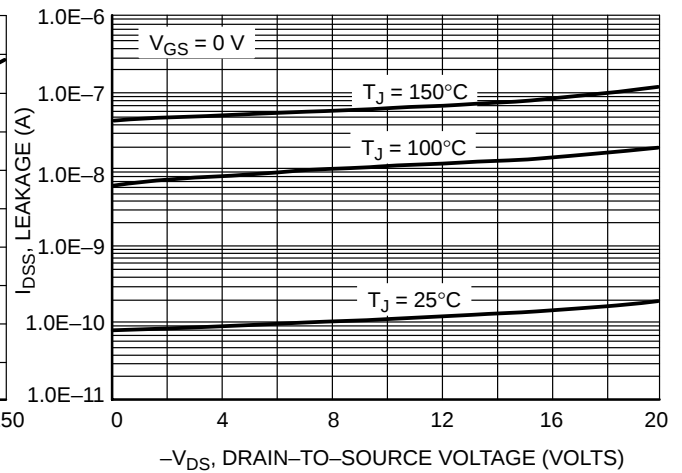
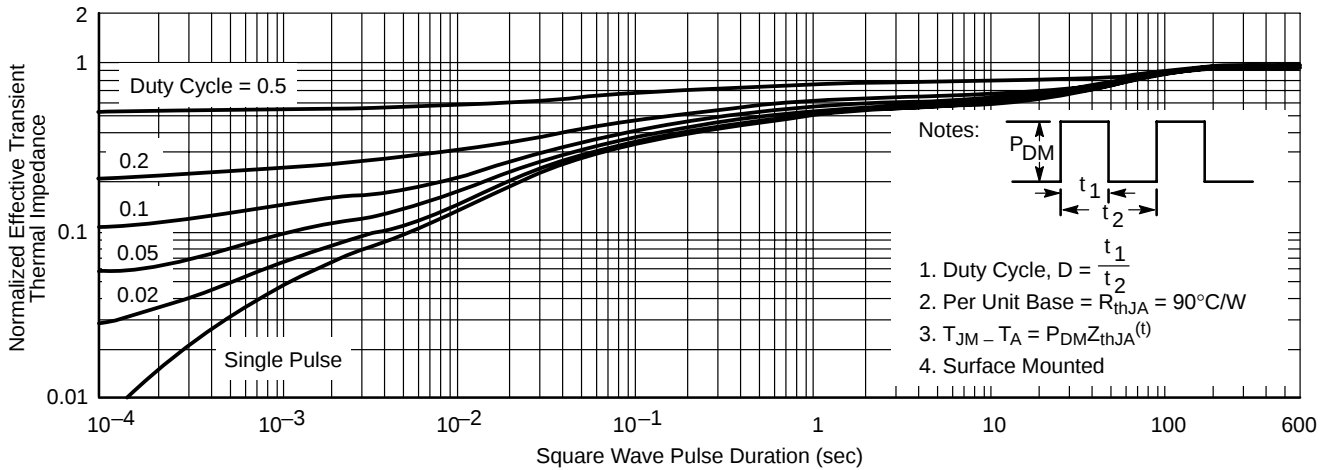
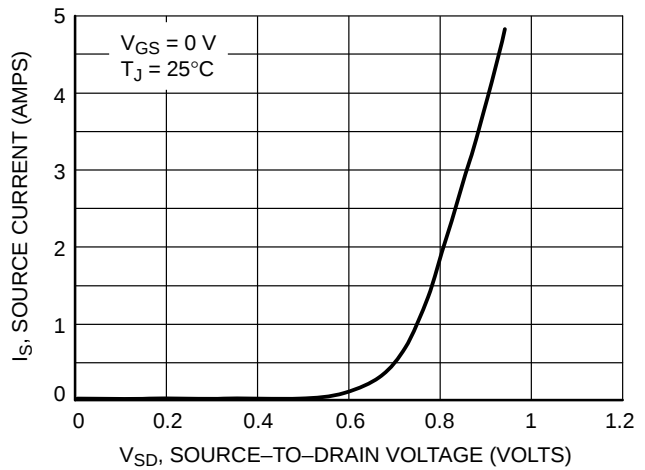
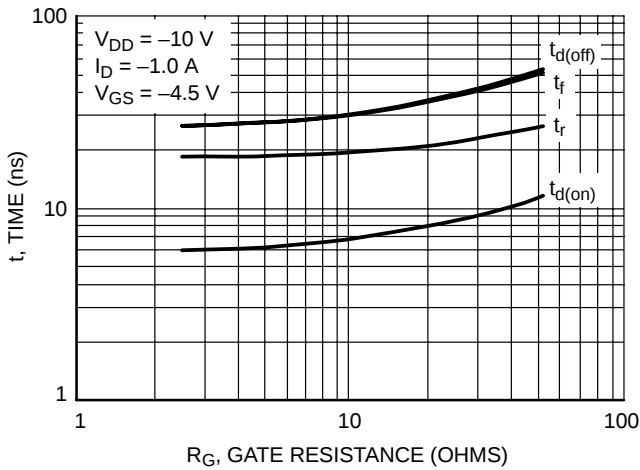
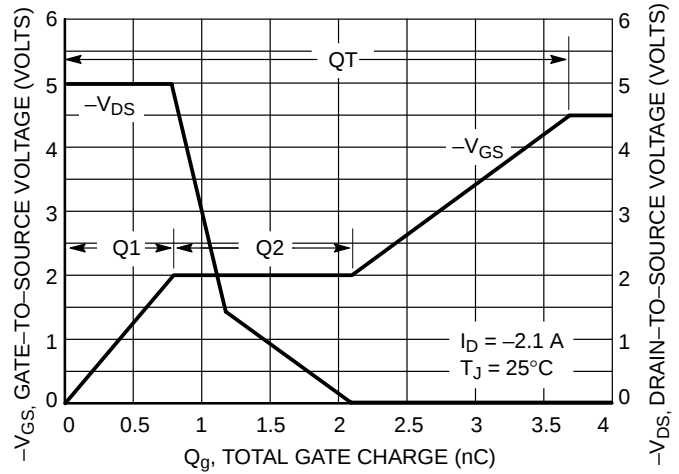
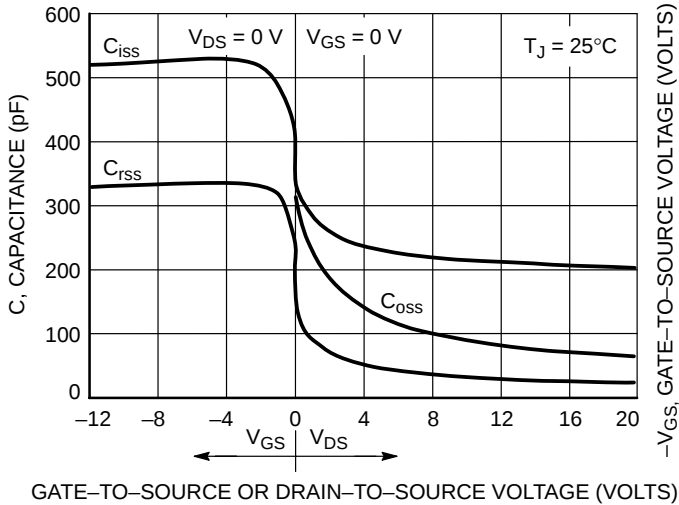


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL ELECTRICAL CHARACTERISTICS



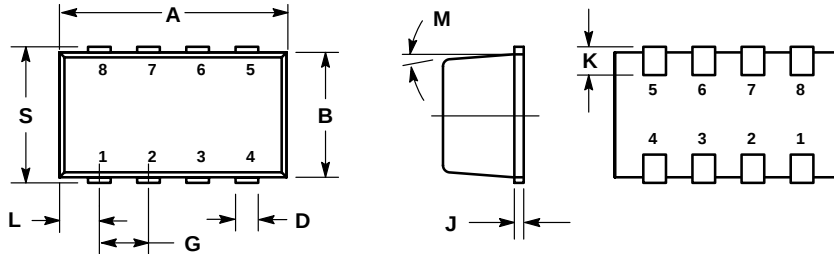
Notes

Notes

NTHD5903T1

PACKAGE DIMENSIONS

ChipFET
CASE 1206A-03
ISSUE D



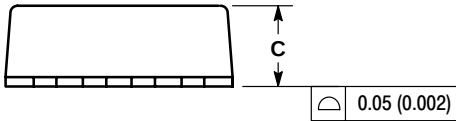
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.
7. 1206A-01 AND 1206A-02 OBSOLETE. NEW STANDARD IS 1206A-03.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.95	3.10	0.116	0.122
B	1.55	1.70	0.061	0.067
C	1.00	1.10	0.039	0.043
D	0.25	0.35	0.010	0.014
G	0.65 BSC		0.025 BSC	
J	0.10	0.20	0.004	0.008
K	0.28	0.42	0.011	0.017
L	0.55 BSC		0.022 BSC	
M	5 ° NOM		5 ° NOM	
S	1.80	2.00	0.072	0.080

STYLE 2:

- PIN 1. SOURCE 1
- GATE 1
- SOURCE 2
- GATE 2
- DRAIN 2
- DRAIN 2
- DRAIN 1
- DRAIN 1



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